TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC74HC40105AP, TC74HC40105AF

4 Bit × 16 Word FIFO Register

The TC74HC40105A is a high speed CMOS 4 bit \times 16 word first-in, first-out (FIFO) Strage Register fabricated with silicon gate C²MOS technology.

It achieves the high speed operation while maintaining the CMOS low power dissipation.

The device is capable of handling 16 four-bit words and it is possible to handle the input and output data at different shifting rates.

When the DATA-IN-READY (DIR) is high, data is written into the registers by a low to high transition of the SHIFT IN (SI) input. And when DATA-OUT-READY (DOR) is high, data is read out of the registers by a high to low transition of the \overline{SHIFT} \overline{OUT} (\overline{SO}) input.

If the MASTER RESET (MR) is high, the DIR goes high and DOR goes low. The data in the internal registers are not changed but are declared invalid.

The TC74HC40105A can be cascaded to form longer registers or wider words.

The DATA OUTPUTs (Qn) are 3-State Outputs. When \overline{OUTPUT} ENABLE (\overline{OE}) is held high, the Qn's are in high impedance state.

All inputs are equipped with protection circuits against static discharge or transient excess voltage.

Features

- High speed: f_{max} 25 MHz (typ.) at $V_{CC} = 5 \text{ V}$
- Low power dissipation: $I_{CC} = 4 \mu A \text{ (max)}$ at $T_a = 25 \text{°C}$
- High noise immunity: V_{NIH} = V_{NIL} = 28% V_{CC} (min)
- Output drive capability: 10 LSTTL loads for DIR, DOR

15 LSTTL loads for Q0 to Q3

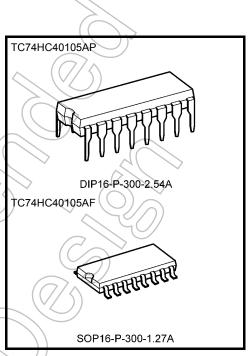
• Symmetrical output impedance: | IOH | = IOL = 4 mA (min)

for DIR, DOR

 $|I_{OH}| = I_{OL} = 6 \text{ mA (min)}$

for Q0 to Q3

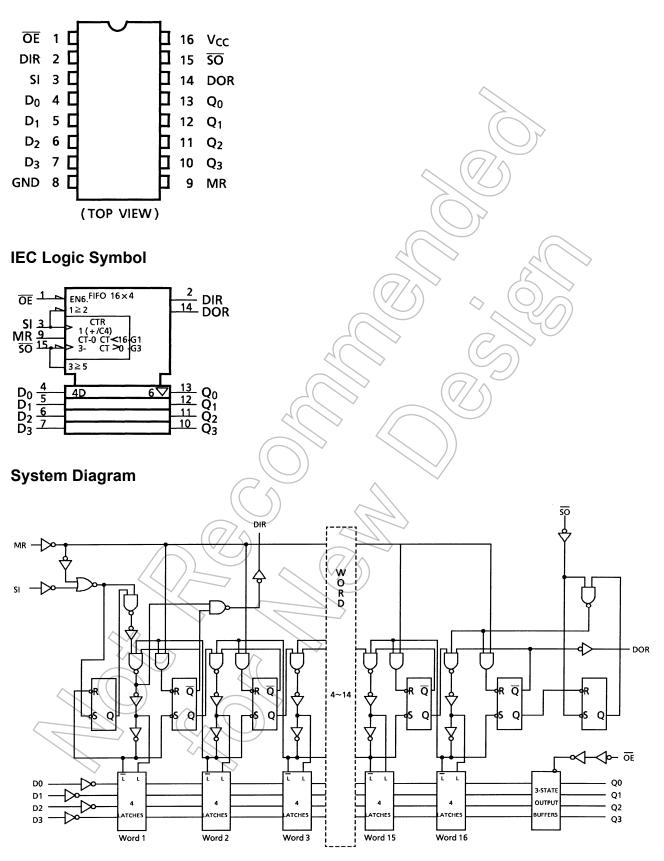
- Balanced propagation delays: $t_{pLH} \simeq t_{pHL}$
- Wide operating voltage range: VCC (opr) = 2 to 6 V



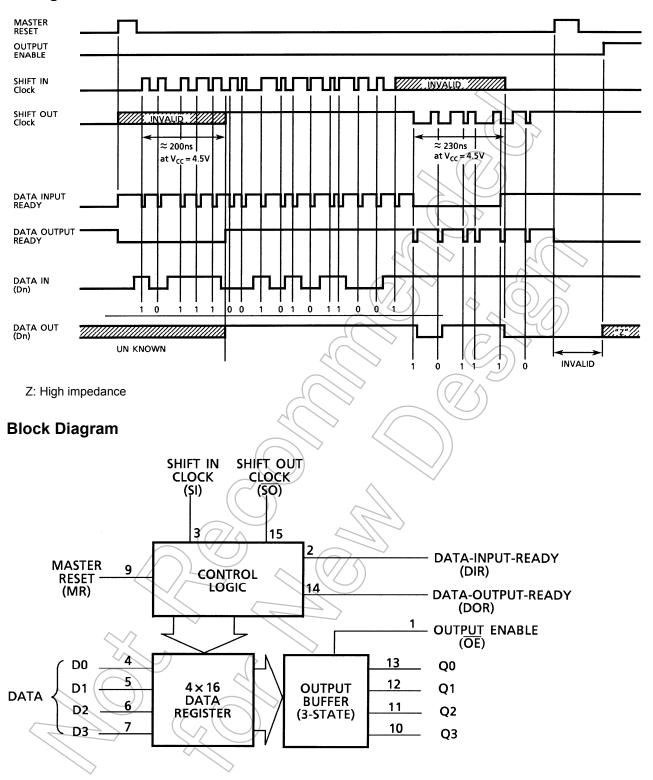
Weight

DIR16-P-300-2.54A : 1.00 g (typ.) SOP16-P-300-1.27A : 0.18 g (typ.)

Pin Assignment



Timing Chart



Functional Description

(1) Writing data

Data can be written into the FIFO whenever DIR is high and a low to high transition occurs on the SI pin.

DIR will toggle momentarily until the data has been transferred to the second word register.

SI must be toggled before the next 4-bit word can be written. The first and subsequent words will automatically ripple to the output end of the device even if there is not a full 16 words of input data. When all 16 words are filled with data, DIR will go low and additional data cannot be written into the device.

(2) Reading data

When a data word appears in the sixteenth data register (just before the output buffer), DOR goes high and, if \overline{OE} is low, data can be output on the high to low transition of \overline{SO} .

The data remaining in the registers now ripples to the next higher word position opening the first word position for new data. DIR goes high and additional data can be written in. During the output of data, \overline{DOR} toggles momentarily after each read. When the data registers become empty, \overline{DOR} goes low and \overline{SO} is ignored.

(3) Master rest

When a high is input to MR, the internal control logic is initialized. This causes DIR to go high and DOR to go low. The contents of the data registers are not changed, but are invalid and will be written over when the first word is loaded.

(4) Cascading

The TC74HC40105A can be cascaded to form longer registers simply by connecting DOR of the first device to SI of the second and DIR of the second device to \overline{SO} of the first. Additional devices may be cascaded by repeating the above. Of course, the Qn outputs of the first device must be connected to the Dn inputs of the second.

In this mode, an MR pulse must be applied after the supply voltage is turned on. For words wider than 4-bits, the DIR and DOR outputs from each FIFO must be ANDed respectively and the SI and \overline{SO} inputs must each be paralleled.

Absolute Maximum Ratings (Note 1)

Characteristics	Symbol	Rating	Unit
Supply voltage range	√V _{CC}	-0.5 to 7	V
DC input voltage		-0.5 to V _{CC} + 0.5	V
DC output voltage	Vout <	-0.5 to V _{CC} + 0.5	V
Input diode current	I _{IK}	±20	mA
Output diode current	lok	±20	mA
DC output current (DIR, DOR)	lou-	±25	mA
(Q0 to Q3)	Гоит	±35	ША
DC V _{CC} /ground current	1CC	±75	mA
Power dissipation	PD	500 (DIP) (Note 2)/180 (SOP)	mW
Storage temperature	T _{stg}	-65 to 150	°C

Note 1: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 2: 500 mW in the range of Ta = -40 to 65° C. From Ta = 65 to 85° C a derating factor of -10 mW/°C shall be applied until 300 mW.



Operating Ranges (Note)

Characteristics	Symbol	Rating	Unit
Supply voltage	V_{CC}	2 to 6	V
Input voltage	V _{IN}	0 to V _{CC}	V
Output voltage	V _{OUT}	0 to V _{CC}	(V
Operating temperature	T _{opr}	−40 to 85	°C
		0 to 1000 (V _{CC} = 2.0 V)	
Input rise and fall time	t _r , t _f	0 to 500 (V _{CC} = 4.5 V)	ns
		0 to 400 (V _{CC} = 6.0 V)	$\langle \rangle \rangle$

Note: The operating ranges must be maintained to ensure the normal operation of the device. Unused inputs must be tied to either V_{CC} or GND.

Electrical Characteristics

DC Characteristics

		r		$-$ \ \vee /	, , ,	\rightarrow		46	_	
Characteristics	Symbol	Te	est Condition		<u> </u>	Ta = 25°0			a ⊨ 85°C	Unit
Characteristics	Cymbol		V _{CC} (V)	Min	Typ.	Max	Min	Max		
High lavel innex			2.0	1.50			1.50	_		
High-level input voltage	V_{IH}	-	-7(//	4.5	3.15) —	3.15	_	V
			400	6.0	4.20		/ —	4.20		
Low lovel input				2.0	_ \	//-	0.50		0.50	
Low-level input voltage	V_{IL}			4.5		//-	1.35	_	1.35	V
				6.0		/ —	1.80	_	1.80	
		, ((\	1	2.0	1.9	2.0	_	1.9	_	
		V _{IN} = V _{IH} or V _{IL}	I _{OH} = -20 μA	4.5	4.4	4.5	_	4.4	_	
	($(7/\Delta)$		6.0	5.9	6.0	_	5.9	_	
High-level output voltage	VOH	(DIR	$I_{OH} = -4 \text{ mA}$	4.5	4.18	4.31	_	4.13	_	V
		DOR)	$I_{OH} = -5.2 \text{ mA}$	6.0	5.68	5.80		5.63	_	
		(Q0 to	$I_{OH} = -6 \text{ mA}$	4.5	4.18	4.31	_	4.13	_	
		Q3)	$I_{OH} = -7.8 \text{ mA}$	6.0	5.68	5.80		5.63	_	
\sim	2			2.0	_	0.0	0.1	_	0.1	
\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	5	V _{IN} = V _{IH} or V _{IL}	$I_{OL} = 20 \mu A$	4.5	_	0.0	0.1	_	0.1	
		4		6.0	_	0.0	0.1	_	0.1	
Low-level output voltage)) v _{oL}	(DIR	I _{OL} = 4 mA	4.5	_	0.17	0.26	_	0.33	V
		DOR)	I _{OL} = 5.2 mA	6.0	_	0.18	0.26	_	0.33	
		(Q0 to	I _{OL} = 6 mA	4.5	_	0.17	0.26	_	0.33	
		Q3)	I _{OL} = 7.8 mA	6.0	_	0.18	0.26	_	0.33	
3-state output off-state current	I _{OZ}	V _{IN} = V _{IH} or V _{IL} V _{OUT} = V _{CC} or GND		6.0	_	_	±0.5	_	±5.0	μА
Input leakage current	I _{IN}	$V_{IN} = V_{CC}$ or C	6.0	_	_	±0.1	_	±1.0	μА	
Quiescent supply current	I _{CC}	$V_{IN} = V_{CC}$ or C	GND	6.0	_	_	4.0	_	40.0	μА



Timing Requirements (input: $t_r = t_f = 6$ ns)

Characteristics	Symbol	Test Condition		Ta =	25°C	Ta = -40 to 85°C	Unit
			V _{CC} (V)	Тур.	Limit	Limit	
Minimum pulse width	t _{W (L)}		2.0	_	75	95	
(SI)	tw (L)	_	4.5	<u> </u>	15	19	ns
(01)	۷۷ (ロ)		6.0		13	16	
Minimum pulse width	t _{W (L)}		2.0	(75	95	
(SO)	tw (L)	_	4.5	, , ,	15	19	ns
(00)	۷۷ (ロ)	4	6.0	())	13	16	
Minimum pulse width	t _{W (L)}		2.0		75	95	
(MR)	tw (L)	_	4.5	> —	15	19	ns
(MIX)	۷۷ (H)	6	6.0	_	13	16	
Minimum set-up time		41	2.0	_	46	0	
(DATA-SI)	t_{s}	-	4.5	- /	0	0	ns
(BATTA OI)		(\langle / \rangle)	6.0	-(()0_	0	
Minimum hold time			2.0	(7)	900	125	
(DATA-SI)	t_h		4.5	7	20	25	ns
(BATTA OI)		4()	6.0	<u>/</u>	17	21	
Minimum removal time			2.0		50	65	
(MR-SI)	t_{rem}		4.5) —	10	13	ns
(IVII C-OI)		4()	6.0	_	9	11	
			2.0	_	3	2.4	
Clock frequency	f (4.5	_	15	12	MHz
			6.0		18	13	

AC Characteristics ($C_L = 15 \text{ pF}$, $V_{CC} = 5 \text{ V}$, $Ta = 25 ^{\circ}\text{C}$, input: $t_r = t_f = 6 \text{ ns}$)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Output transition time	t _{TLH}			4	8	ns
(DIR, DOR)	t _{THL}			†	0	110
Propagation delay time				22	39	ns
(SO , MR-DOR)	t _{pHL}	_	_	22	39	115
Propagation delay time	. (>	<u> </u>		242	365	ns
(SO-DIR)	t _{plL} H	_	_	242	303	115
Propagation delay time				187	300	20
(SI-DOR)	(tbrH	_	_	107	300	ns
Propagation delay time				20	25	
(SI-DIR)	t _{pHL}	_	_	22	35	ns
Propagation delay time	t _{pLH}			25	39	20
(MR-DIR)	t _{pHL}			25	39	ns



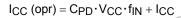
AC Characteristics (input: $t_r = t_f = 6 \text{ ns}$)

Characteristics	Symbol	Test Condition		-	Γa = 25°0		Ta –40 to	Unit		
	- J		CL (pF)	V _{CC} (V)	Min	Тур.	Max	Min	Max	
Outrout transition times	4			2.0	_	21	60	_	75	
Output transition time	t _{TLH}	_	50	4.5	_	7	12	_	15	ns
(Q0 to Q3)	t _{THL}			6.0	_	6	10	_	13	
Outrot transition time				2.0	_	24	75	7	95	
Output transition time	t _{TLH}	_	50	4.5	_	8	15	/)_	19	ns
(DIR, DOR)	t _{THL}			6.0	_	10	13	_	16	
Propagation delay				2.0	_//	84	225	_	280	
time	t _{pHL}	_	50	4.5	-(28	45	_	56	ns
(SO, MR-DOR)				6.0	= /	24)	38	_	48	
Propagation delay				2.0		798	2000	6	2500	
time	t _{pLH}	_	50	4.5	17	266	400	4	500	ns
(SO-DIR)				6.0) ~ >	226	340		425	
Propagation delay				2.0	\mathcal{I}	624	1650	2//	2060	
time	t _{pLH}	_	50	4.5	_	208	330	90	412	ns
(SI-DOR)				6.0	_	177	280	>_	350	
Propagation delay				2.0	_	78	200	_	250	
time	t _{pHL}	_	50	4.5	_	26	40	_	50	ns
(SI-DIR)				6.0	_	22	34	_	43	
				2.0	_	156	400	_	500	
			50	4.5	_) 52	80	_	100	
Propagation delay time	t _{pLH})	6.0		44	68	_	85	
(SO-Qn)	t_{pHL}			2.0	_	171	440	_	550	ns
()			150	4.5	_	57	88	_	110	
		774		6.0	<i>></i> _	48	75	_	94	
		(\bigcirc)		2.0	_	612	1500	_	1875	
	(() _		50//	4.5	_	204	300	_	375	
Propagation delay time	tpLH			6.0	_	173	255	_	319	ns
(SI-Qn)	t _{pHL}			2.0	_	627	1540	_	1925	115
	,		150	4.5	_	209	308	_	385	
	5		\vee	6.0	_	178	262	_	327	
Propagation delay	•	4(2.0	_	87	225	_	280	
time	t _{pLH}		50	4.5	_	29	45	_	56	ns
(MR-DIR)	t _{pHL}			6.0	_	25	38		48	
	()			2.0	_	45	125	_	155	
			50	4.5	_	15	25		31	
Output enable time	t_{pZL}	$R_L = 1 k\Omega$		6.0	_	13	21		26	ns
Output chable tille	t _{pZH}	N_		2.0	_	60	165	_	205	113
			150	4.5	_	20	33		41	
				6.0	_	17	28	_	35	
	+ . =			2.0	_	32	125	_	155	
Output disable time	t _{pLZ}	$R_L = 1 \text{ k}\Omega$	50	4.5	_	16	25	_	31	ns
	t _{pHZ}			6.0	_	14	21	_	26	

Characteristics	Symbol	Symbol Test Condition		Ta = 25°C			Ta = -40 to 85°C		Unit	
	ŕ		CL (pF)	V _{CC} (V)	Min	Тур.	Max	Min	Max	
				2.0	3	7	_	2.4	_	
			50	4.5	15	22	_	12	_	
Maximum clock	f _{max}	_		6.0	18	26	_	14	_	MHz
frequency	ımax	_		2.0	2.6	6	1	2	_	IVIII
			150	4.5	13	20	(10	_	
				6.0	15	24	1))12	_	
Output pulse width	Outrot pulse width			2.0	_	95	,) \	_	_	
(DIR)	t _{w (H)}	_	50	4.5		25	\mathcal{A}	_	_	ns
(DIK)	t _{w (L)}			6.0	-(21)			
Output pulse width	t an			2.0	_/	95)	_	_	_	
(DOR)	t _{w (H)}	_	50	4.5		25	_	F	_	ns
(DOK)	(DOR) $t_{w(L)}$			6.0	1	21	_	4	/	
Input capacitance	C _{IN}	-	_		\ 	5	10		> 10	pF
Output capacitance	C _{OUT}	-	_))	10 🔷		245) —	pF
Power dissipation capacitance	C _{PD}			(Note)		300		50	_	pF

Note: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

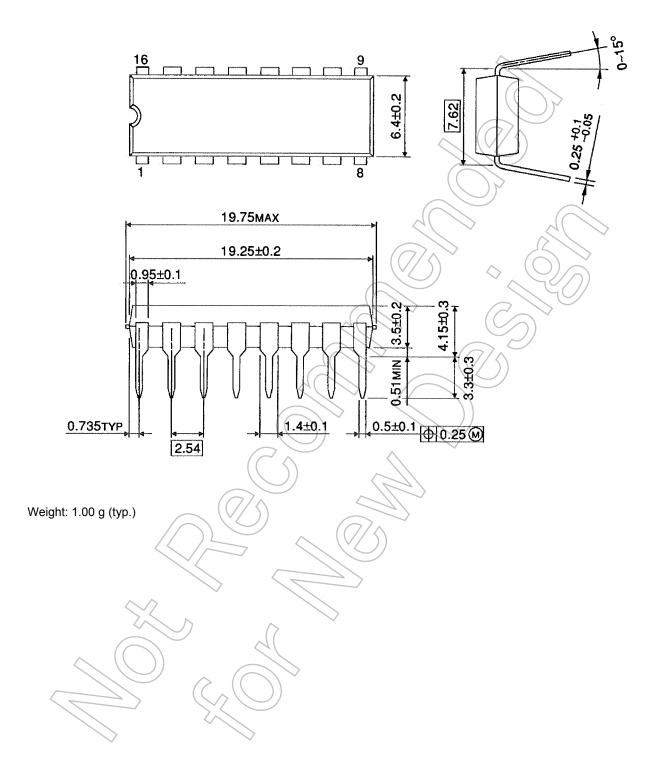
Average operating current can be obtained by the equation:





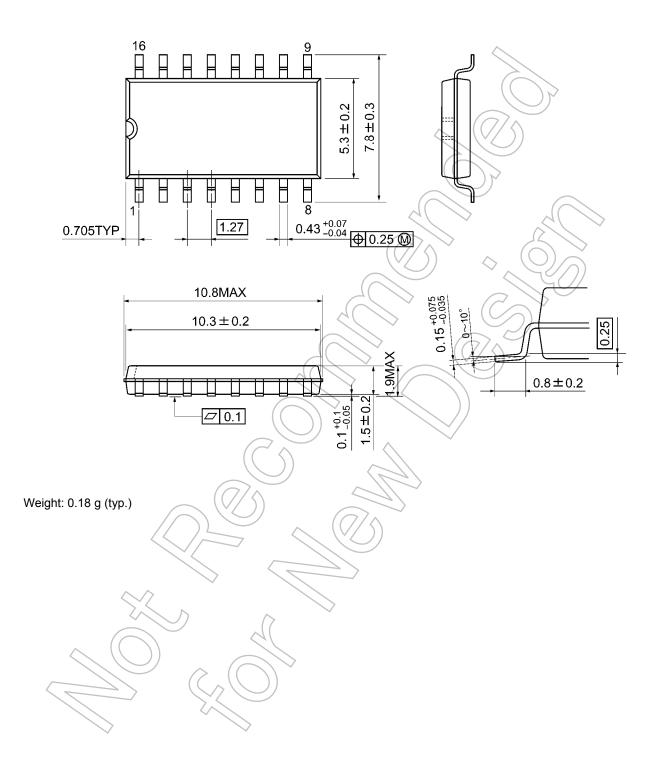
Package Dimensions

DIP16-P-300-2.54A Unit: mm



Package Dimensions

SOP16-P-300-1.27A Unit: mm



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